

IN THE CLAIMS:

Please amend the claims as follows.

Claim 1 (Canceled).

Claim 2 (Currently Amended): The photodiode array according to Claim 5 ~~[[1]]~~, wherein a plurality of depressions having a predetermined depth are formed in array on the opposite surface side to the incidence surface of the light to be detected, in the semiconductor substrate, and

wherein each said photodiode is formed in a bottom portion of the associated depression.

Claim 3 (Currently Amended): The photodiode array according to Claim 5 ~~1 or 2~~, wherein the projection is made of a resin or metal having a light blocking property.

Claim 4 (Currently Amended): The photodiode array according to Claim 5 ~~[[1]]~~, wherein the projection comprises a plurality of projections, and

wherein the projections are discontinuously arranged at predetermined intervals.

Claim 5 (Currently Amended): A photodiode array comprising a semiconductor substrate,

wherein a plurality of photodiodes are formed in array on an opposite surface side to an incidence surface of light to be detected, in the semiconductor substrate,

wherein a projection having a predetermined height is provided in a region not corresponding to regions where the photodiodes are formed, on a side of the incidence surface of the light to be detected, in the semiconductor substrate, and

~~The photodiode array according to Claim 1~~[[,]] wherein the semiconductor substrate is provided with an impurity region between the photodiodes adjacent to each other, for separating the photodiodes from each other.

Claim 6 (Currently Amended): A photodiode array comprising a semiconductor substrate,

wherein a plurality of photodiodes are formed in array on an opposite surface side to an incidence surface of light to be detected, in the semiconductor substrate,

wherein a projection having a predetermined height is provided in a region not corresponding to regions where the photodiodes are formed, on a side of the incidence surface of the light to be detected, in the semiconductor substrate, and

~~The photodiode array according to Claim 1~~[[,]] wherein a high-impurity-concentration layer of the same conductivity type as the semiconductor substrate is formed on the incidence surface side of the light to be detected, in the semiconductor substrate.

Claim 7 (Withdrawn): A method of producing a photodiode array, the method comprising:

a step of preparing a semiconductor substrate comprised of a semiconductor of a first conductivity type;

a step of forming a plurality of impurity diffused layers of a second conductivity type on one surface side of the semiconductor substrate to form a plurality of photodiodes each comprised of the impurity diffused layer and the semiconductor substrate, in array; and

a step of providing a projection having a predetermined height, in a region not corresponding to regions where the photodiodes are formed, on another surface of the semiconductor substrate.

Claim 8 (Withdrawn): A method of producing a photodiode array, the method comprising:

a step of preparing a semiconductor substrate comprised of a semiconductor of a first conductivity type;

a step of forming a plurality of depressions in array on one surface side of the semiconductor substrate;

a step of forming a plurality of impurity diffused layers of a second conductivity type in bottom portions of the depressions to form a plurality of photodiodes each comprised of the impurity diffused layer and the semiconductor substrate, in array; and

a step of providing a projection having a predetermined height, in a region not corresponding to regions where the photodiodes are formed, on another surface of the semiconductor substrate.

Claim 9 (Withdrawn): The method according to Claim 7 or 8, further comprising a step of forming a high-impurity-concentration layer of the first conductivity type on the other surface of the semiconductor substrate, prior to the step of providing the projection.

Claim 10 (Withdrawn): The method according to Claim 7, further comprising a step of providing an impurity region of the first conductivity type between the impurity diffused layers adjacent to each other.

Claim 11 (Currently Amended): A photodiode array comprising a semiconductor substrate,

wherein a plurality of photodiodes are formed in array on an opposite surface side to an incidence surface of light to be detected, in the semiconductor substrate,

wherein a projection having a predetermined height is provided in a region not corresponding to regions where the photodiodes are formed, on a side of the incidence surface of the light to be detected, in the semiconductor substrate, and

~~A radiation detector comprising:~~

~~the photodiode array as set forth in Claim 1; and~~

a scintillator panel arranged opposite to the incidence surface of the light to be detected, in the photodiode array, and arranged to emit light with incidence of radiation.

Claim 12 (Withdrawn): A radiation detector comprising:
the photodiode array produced by the method as set forth in Claim 7; and
a scintillator panel arranged opposite to the surface where the projection is provided in
the photodiode array, and arranged to emit light with incidence of radiation.

Claim 13 (New): The photodiode array according to Claim 6, wherein a plurality of
depressions having a predetermined depth are formed in array on the opposite surface side to the
incidence surface of the light to be detected, in the semiconductor substrate, and
wherein each said photodiode is formed in a bottom portion of the associated depression.

Claim 14 (New): The photodiode array according to Claim 6, wherein the projection is
made of a resin or metal having a light blocking property.

Claim 15 (New): The photodiode array according to Claim 6, wherein the projection
comprises a plurality of projections, and
wherein the projections are discontinuously arranged at predetermined intervals.

Claim 16 (New): The photodiode array according to Claim 11, wherein a plurality of
depressions having a predetermined depth are formed in array on the opposite surface side to the
incidence surface of the light to be detected, in the semiconductor substrate, and
wherein each said photodiode is formed in a bottom portion of the associated depression.

Claim 17 (New): The photodiode array according to Claim 11, wherein the projection is made of a resin or metal having a light blocking property.

Claim 18 (New): The photodiode array according to Claim 11, wherein the projection comprises a plurality of projections, and

wherein the projections are discontinuously arranged at predetermined intervals.